IN THE CLAIMS:

1. (Currently Amended) A hybrid substrate comprising:

a carrier substrate having a plurality of pockets patterned thereon; and

at least two substrates, each substrate being formed from a different material and being deposited within a separate pocket of the plurality of pockets such that at least a portion of the at least two substrates protrudes above the surface of the carrier substrate, for fabricating a plurality of devices.

2. (Previously Presented) The hybrid substrate according to Claim 1, wherein the at least two substrates are different from each other and are approximately co-planar with a top surface of the carrier substrate.

3. (Previously Presented) The hybrid substrate according to Claim 1, wherein the at least two substrates are different from each other and are bonded to the carrier substrate.

4. (Previously Presented) The hybrid substrate according to Claim 1, wherein each of the at least two different substrates are selected from the group consisting of GaAs, InP, silicon (Si), substrate materials for optoelectronic devices, and GaN-based substrate materials for high-electron mobility transistors (HEMTs).

5. (Previously Presented) The hybrid substrate according to Claim 1, wherein the carrier substrate is selected from the group consisting of AlN, quartz, glass, ceramic, CVD diamond, and sapphire.

6. (Previously Presented) The hybrid substrate according to Claim 1, wherein the carrier substrate is a high thermal conductive substrate.

7. (Cancelled)

8. (Withdrawn) A method for fabricating a hybrid substrate comprising the steps of:

patterning a substrate with a plurality of pockets; and

providing a material within each of the plurality of pockets, wherein at least two materials provided within two respective pockets of the plurality of pockets are different.

9. (Withdrawn) The method according to Claim 8, further comprising the step of planarizing the materials provided within each of the plurality of pockets, such that a top surface of the materials is approximately co-planar with a top surface of the substrate.

10. (Withdrawn) The method according to Claim 9, wherein the planarizing step includes a chem-mech polishing step.

11. (Withdrawn) The method according to Claim 8, further comprising the step of providing a thermal conductivity layer between the substrate and the material provided within each of the plurality of pockets.

12. (Withdrawn) The method according to Claim 10, wherein the thermal conductivity layer is a CVD diamond layer.

13. (Withdrawn) The method according to Claim 8, further comprising the step of providing a layer of oxide over the material provided within each of the plurality of pockets.

14. (Withdrawn) The method according to Claim 13, wherein the layer of oxide is a layer of CVD oxide.

15. (Withdrawn) The method according to Claim 8, further comprising the step of providing an oxide on at least one surface of each material before the step of providing the material within each of the plurality of pockets.

16. (Withdrawn) The method according to Claim 8, further comprising the step of annealing to adhere the material provided within each of the plurality of pockets to the substrate.

17. (Withdrawn) The method according to Claim 8, further comprising the step of preparing the material provided within each of the plurality of pockets with the blister separation method.

18. (Withdrawn) The method according to Claim 8, further comprising the step of applying interconnect structures between the materials provided within the plurality of pockets.

19. (Previously Presented) The hybrid substrate according to Claim 1, wherein each pocket of the plurality of pockets has a greater surface area than a surface area of a cross-section of a substrate deposited within that pocket.

20. (Previously Presented) The hybrid substrate according to Claim 1, wherein the at least two substrates and the carrier substrate are each formed from a different material.